

To all our customers

Regarding the change of names mentioned in the document, such as Mitsubishi Electric and Mitsubishi XX, to Renesas Technology Corp.

The semiconductor operations of Hitachi and Mitsubishi Electric were transferred to Renesas Technology Corporation on April 1st 2003. These operations include microcomputer, logic, analog and discrete devices, and memory chips other than DRAMs (flash memory, SRAMs etc.)

Accordingly, although Mitsubishi Electric, Mitsubishi Electric Corporation, Mitsubishi Semiconductors, and other Mitsubishi brand names are mentioned in the document, these names have in fact all been changed to Renesas Technology Corp. Thank you for your understanding. Except for our corporate trademark, logo and corporate statement, no changes whatsoever have been made to the contents of the document, and these changes do not constitute any alteration to the contents of the document itself.

Note : Mitsubishi Electric will continue the business operations of high frequency & optical devices and power devices.

Renesas Technology Corp.
Customer Support Dept.
April 1, 2003

BCR2PM

LOW POWER USE
INSULATED TYPE, PLANAR PASSIVATION TYPE

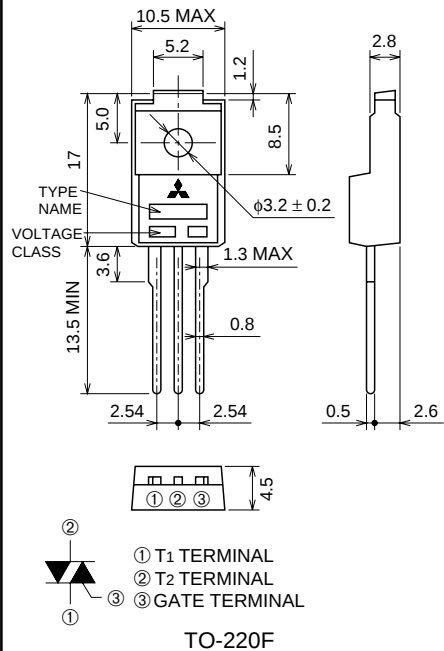
BCR2PM



- IT (RMS) 2A
- VDRM 600V
- IRGT I, IRGT III 10mA

OUTLINE DRAWING

Dimensions
in mm



APPLICATION

Switching mode power supply, light dimmer, electric flasher unit,
control of household equipment such as TV sets · stereo · refrigerator · washing machine · infrared
kotatsu · carpet, solenoid drivers, small motor control,
copying machine, electric tool,
other general purpose control applications

MAXIMUM RATINGS

Symbol	Parameter	Voltage class	Unit
		12	
VDRM	Repetitive peak off-state voltage *1	600	V
VDSM	Non-repetitive peak off-state voltage *1	720	V

Symbol	Parameter	Conditions	Ratings	Unit
IT (RMS)	RMS on-state current	Commercial frequency, sine full wave 360° conduction	2	A
ITSM	Surge on-state current	60Hz sinewave 1 full cycle, peak value, non-repetitive	10	A
I ² t	I ² t for fusing	Value corresponding to 1 cycle of half wave 60Hz, surge on-state current	0.41	A ² s
PGM	Peak gate power dissipation		1	W
PG (AV)	Average gate power dissipation		0.1	W
VGM	Peak gate voltage		6	V
IGM	Peak gate current		1	A
Tj	Junction temperature		-40 ~ +125	°C
Tstg	Storage temperature		-40 ~ +125	°C
—	Weight	Typical value	2.0	g

*1. Gate open.

Mar.2002

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LOW POWER USE

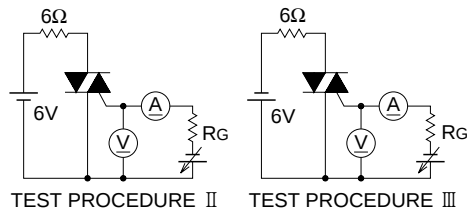
INSULATED TYPE, PLANAR PASSIVATION TYPE

ELECTRICAL CHARACTERISTICS

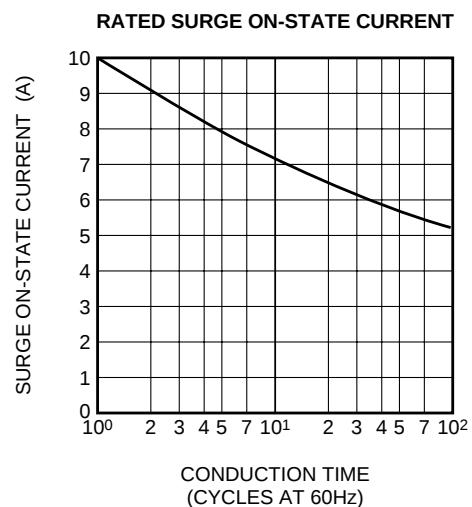
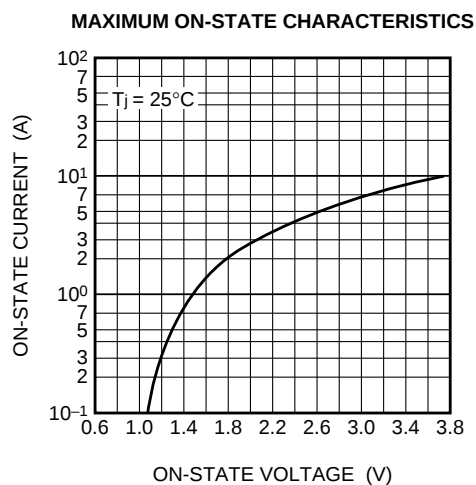
Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
I_{DRM}	Repetitive peak off-state current	$T_J=125^{\circ}\text{C}$, V_{DRM} applied	—	—	0.5	mA
V_{TM}	On-state voltage	$T_a=25^{\circ}\text{C}$, $I_{TM}=1.5\text{A}$, Instantaneous measurement	—	—	1.6	V
$V_{RGT\ I}$	Gate trigger voltage *2	$T_J=25^{\circ}\text{C}$, $V_D=6\text{V}$, $R_L=6\Omega$, $R_G=330\Omega$	—	—	2.0	V
$V_{RGT\ III}$			—	—	2.0	V
$I_{RGT\ I}$	Gate trigger current *2	$T_J=25^{\circ}\text{C}$, $V_D=6\text{V}$, $R_L=6\Omega$, $R_G=330\Omega$	—	—	10	mA
$I_{RGT\ III}$			—	—	10	mA
V_{GD}	Gate non-trigger voltage	$T_J=125^{\circ}\text{C}$, $V_D=1/2V_{DRM}$	0.1	—	—	V
$R_{th(j-a)}$	Thermal resistance	Junction to ambient, Natural convection	—	—	40	$^{\circ}\text{C/W}$

*2. Measurement using the gate trigger characteristics measurement circuit.

GATE TRIGGER CHARACTERISTICS TEST CIRCUITS



PERFORMANCE CURVES

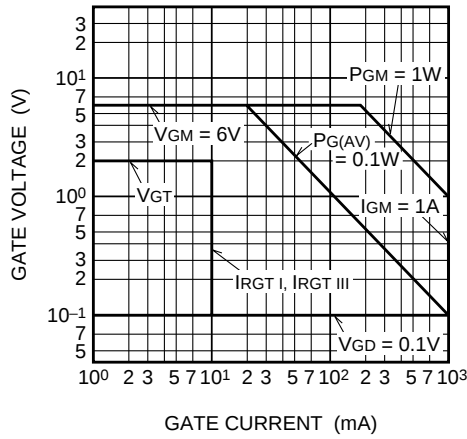


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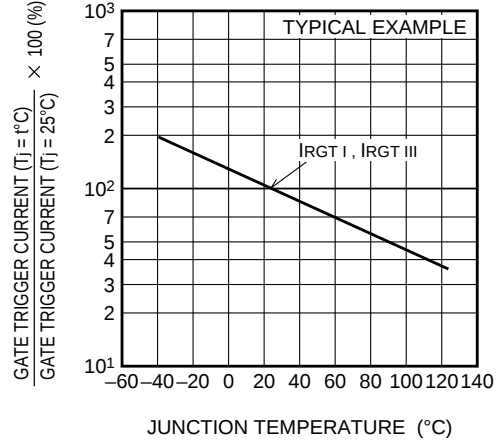
LOW POWER USE

INSULATED TYPE, PLANAR PASSIVATION TYPE

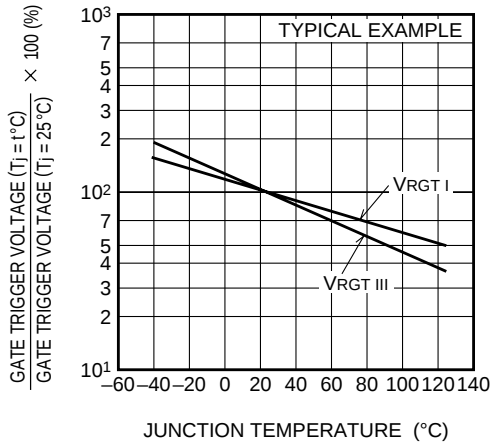
GATE CHARACTERISTICS



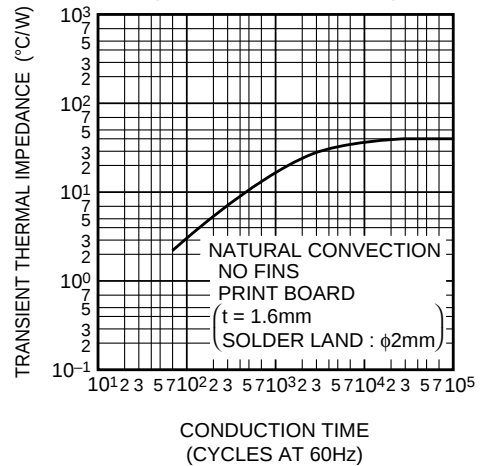
GATE TRIGGER CURRENT VS. JUNCTION TEMPERATURE



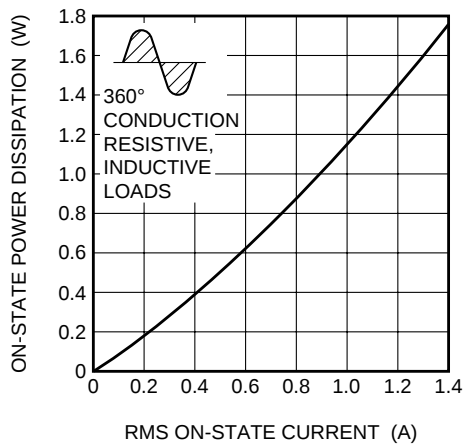
GATE TRIGGER VOLTAGE VS. JUNCTION TEMPERATURE



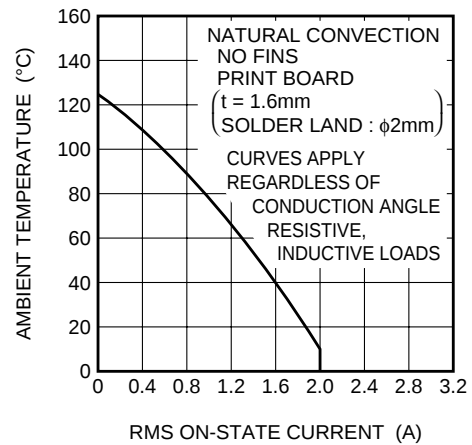
MAXIMUM TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS (JUNCTION TO AMBIENT)



MAXIMUM ON-STATE POWER DISSIPATION



ALLOWABLE AMBIENT TEMPERATURE VS. RMS ON-STATE CURRENT



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